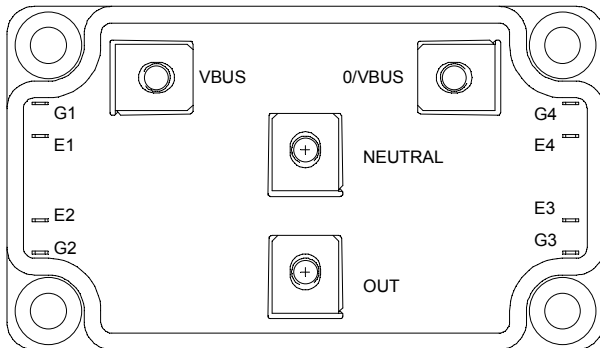
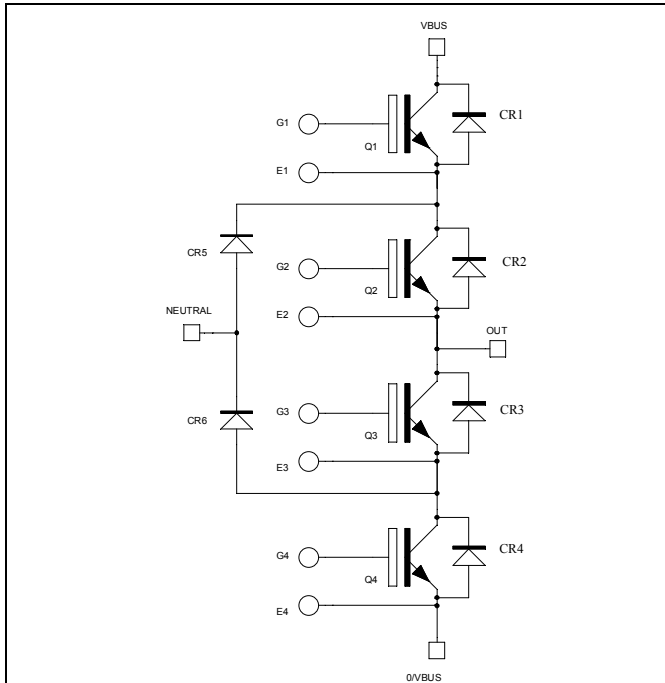


**Three level inverter
Trench + Field Stop IGBT
Power Module**

**$V_{CES} = 600V$
 $I_C = 200A @ T_c = 80^\circ C$**



Application

- Solar converter
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Q1 to Q4 Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	300
		$T_C = 80^\circ C$	200
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	400
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	652
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	400A @ 550V

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Q1 to Q4 Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			350	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 200A$		1.5	1.9	V
		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$		1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 3\text{ mA}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			800	nA

Q1 to Q4 Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		12.2		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		0.78		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.38		
Q_G	Gate charge	$V_{GE} = \pm 15V, I_C = 200A$ $V_{CE} = 300V$		2.2		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 200A$ $R_G = 1.8\Omega$		115		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			225		
T_f	Fall Time			55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 200A$ $R_G = 1.8\Omega$		130		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			300		
T_f	Fall Time			70		
E_{on}	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 200A$	$T_j = 25^\circ\text{C}$	0.8		mJ
			$T_j = 150^\circ\text{C}$	1.75		
E_{off}	Turn off Energy	$R_G = 1.8\Omega$	$T_j = 25^\circ\text{C}$	5		mJ
			$T_j = 150^\circ\text{C}$	7		
I_{sc}	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 360V$ $t_p \leq 6\mu\text{s}; T_j = 150^\circ\text{C}$		1000		A
R_{thJC}	Junction to Case Thermal Resistance				0.23	$^\circ\text{C/W}$

CR1 to CR4 diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	T _j = 25°C T _j = 150°C			150 400	μA
I _F	DC Forward Current		T _c = 80°C		150		A
V _F	Diode Forward Voltage	I _F = 150A V _{GE} = 0V	T _j = 25°C T _j = 150°C		1.6 1.5	2	V
t _{rr}	Reverse Recovery Time	I _F = 150A V _R = 300V di/dt = 2800A/μs	T _j = 25°C T _j = 150°C		100 150		ns
Q _{rr}	Reverse Recovery Charge		T _j = 25°C T _j = 150°C		7.2 15.2		μC
E _{rr}	Reverse Recovery Energy		T _j = 25°C T _j = 150°C		1.7 3.6		mJ
R _{thJC}	Junction to Case Thermal Resistance					0.52	°C/W

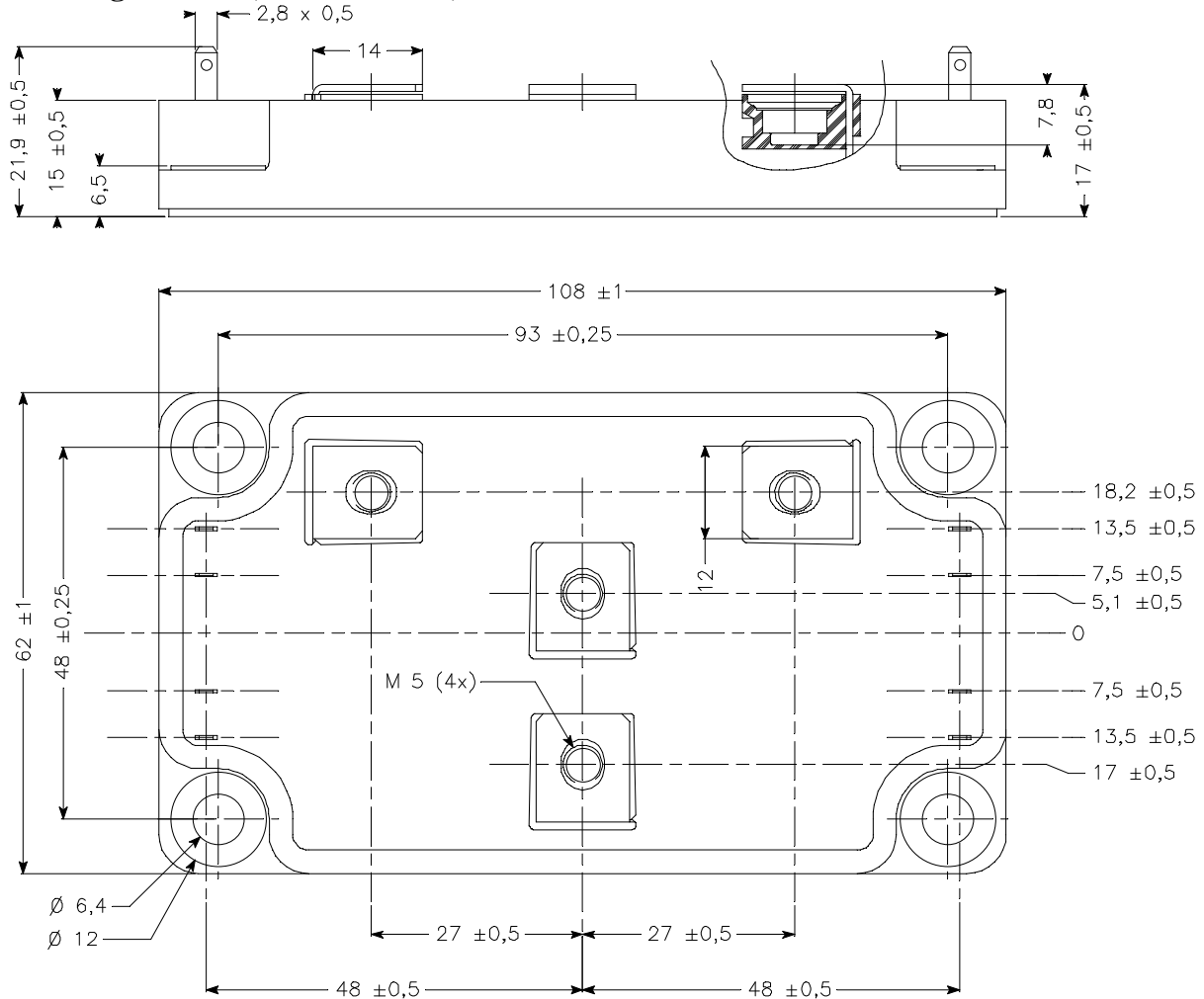
CR5 & CR6 diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	T _j = 25°C T _j = 150°C			150 400	μA
I _F	DC Forward Current		T _c = 80°C		200		A
V _F	Diode Forward Voltage	I _F = 200A V _{GE} = 0V	T _j = 25°C T _j = 150°C		1.6 1.5	2	V
t _{rr}	Reverse Recovery Time	I _F = 200A V _R = 300V di/dt = 2800A/μs	T _j = 25°C T _j = 150°C		125 220		ns
Q _{rr}	Reverse Recovery Charge		T _j = 25°C T _j = 150°C		9.4 19.8		μC
E _{rr}	Reverse Recovery Energy		T _j = 25°C T _j = 150°C		2.2 4.8		mJ
R _{thJC}	Junction to Case Thermal Resistance					0.39	°C/W

Thermal and package characteristics

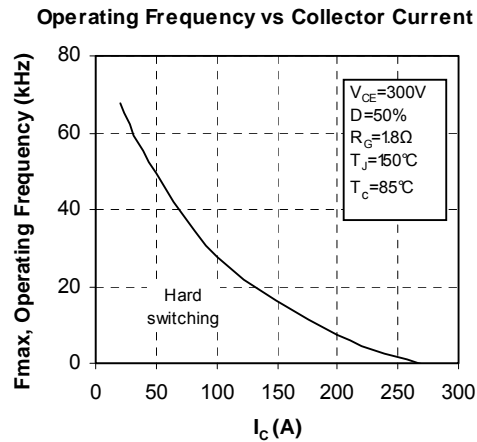
<i>Symbol</i>	<i>Characteristic</i>			<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		175	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					280	g

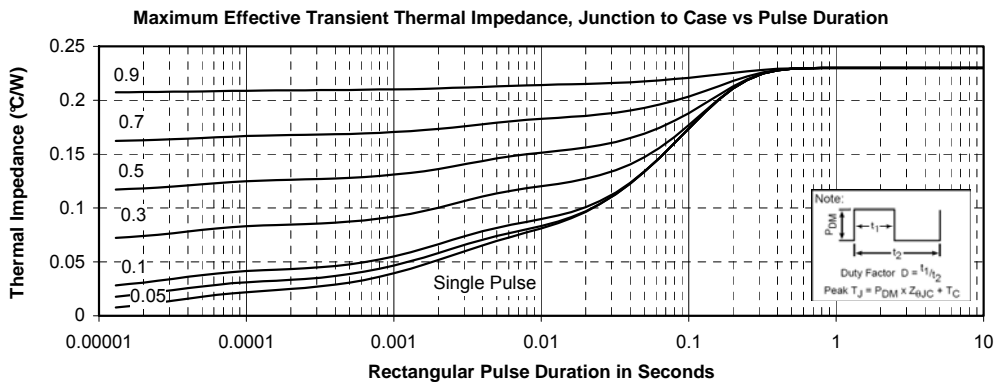
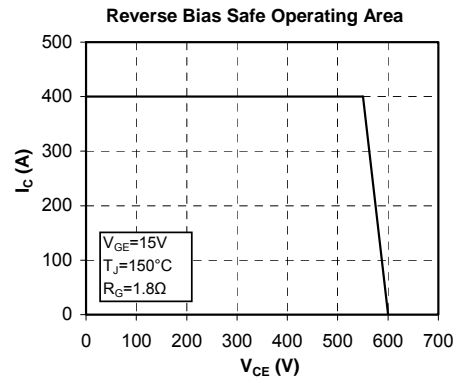
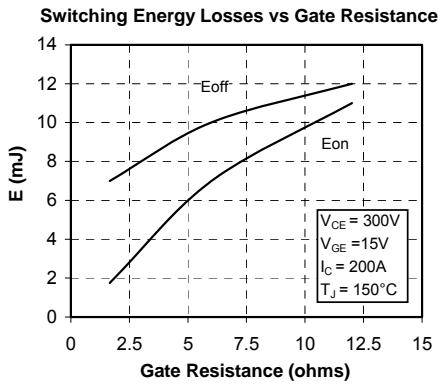
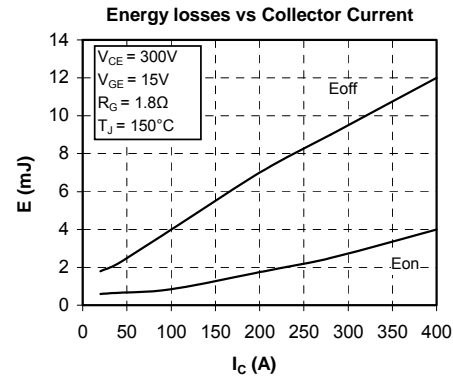
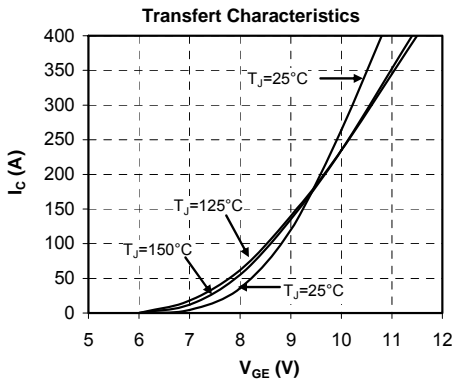
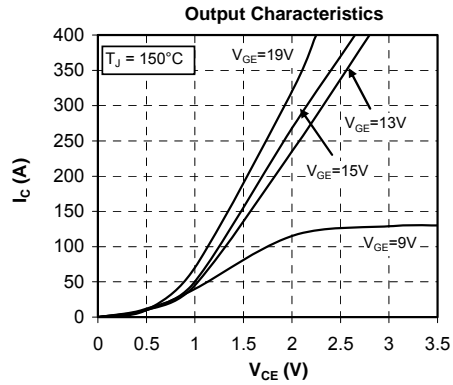
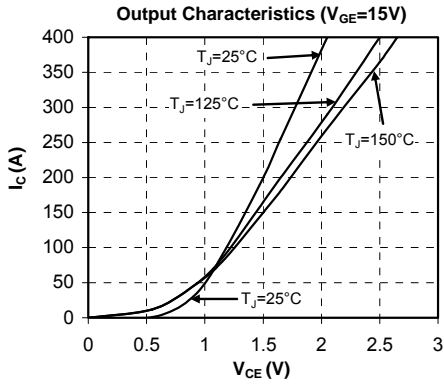
SP6 Package outline (dimensions in mm)

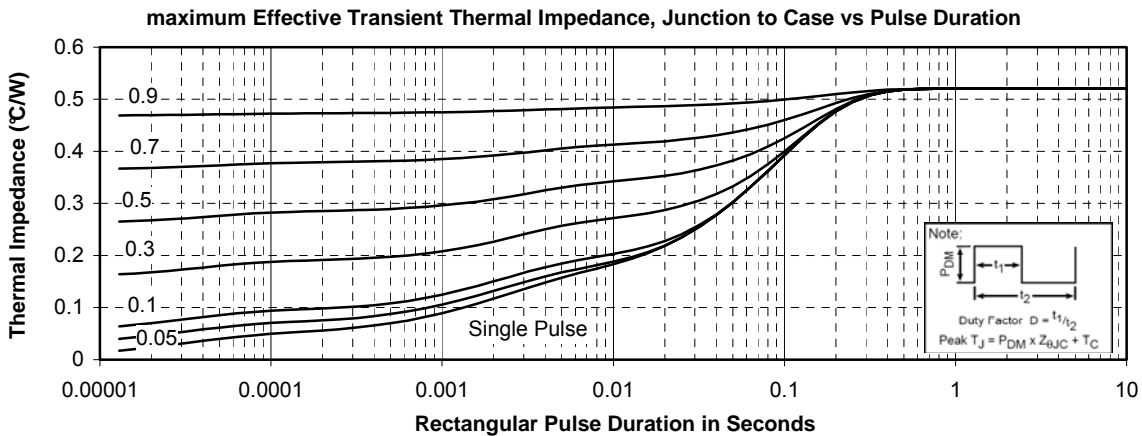
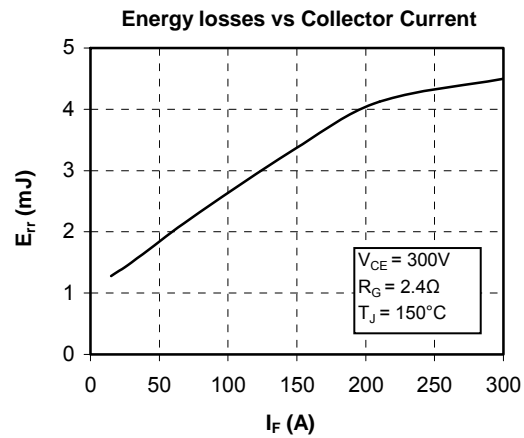
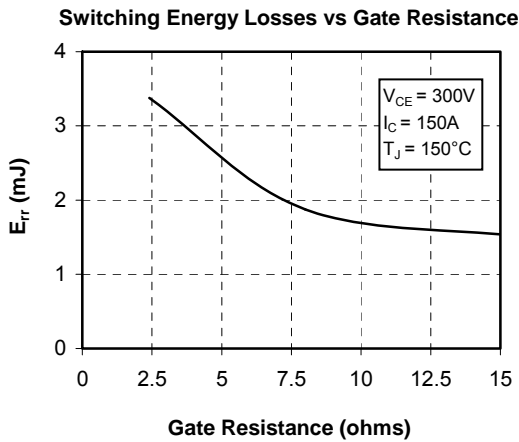
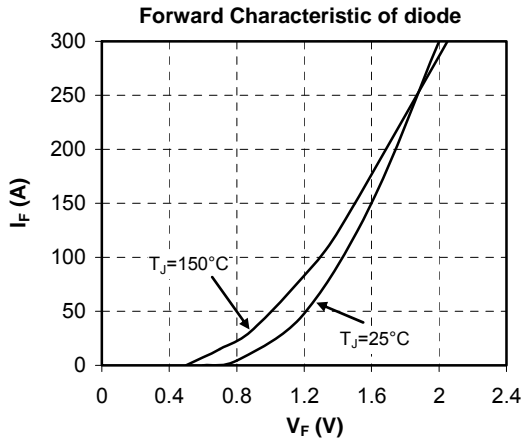


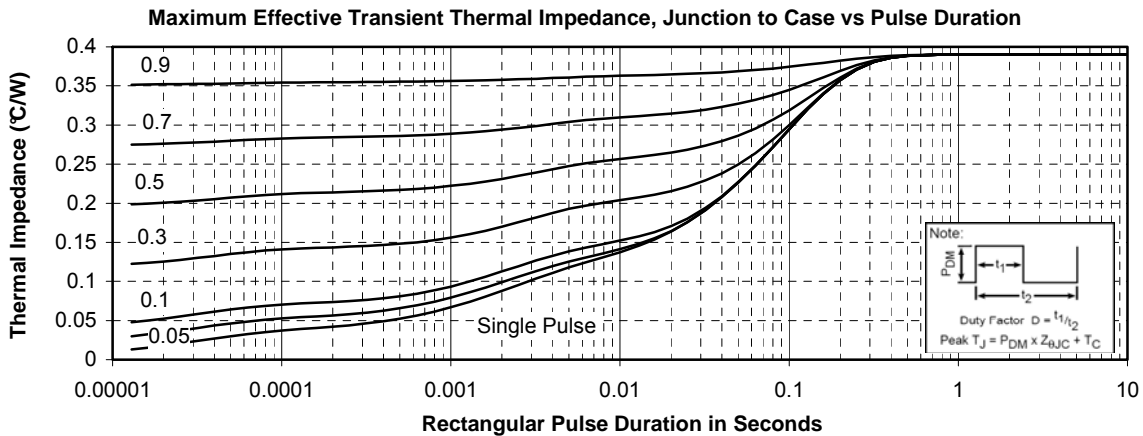
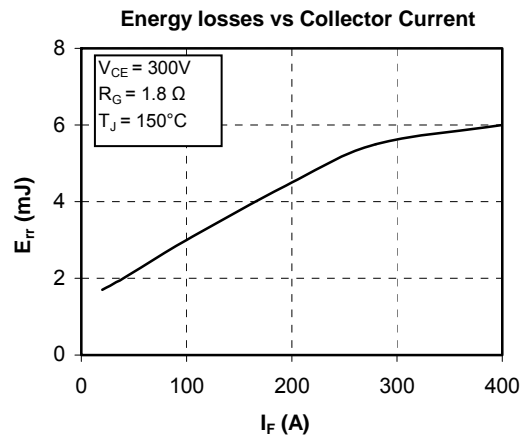
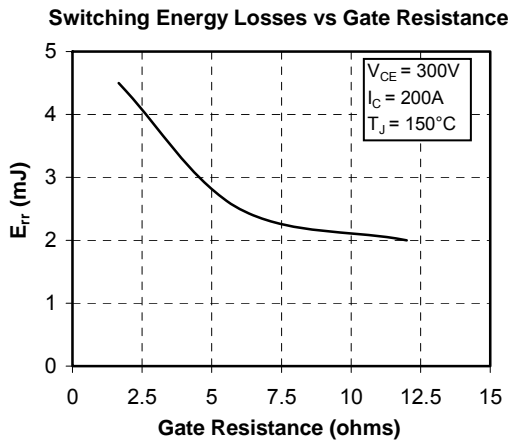
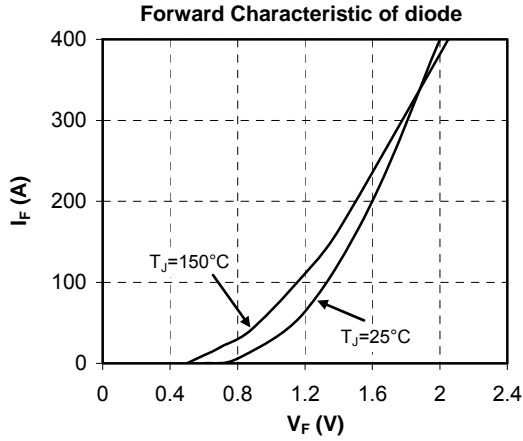
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Q1 to Q4 Typical performance curve





CR1 to CR4 Typical performance curve


CR5 & CR6 Typical performance curve


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